

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	10mΩ@10V	45A
	13mΩ@4.5V	

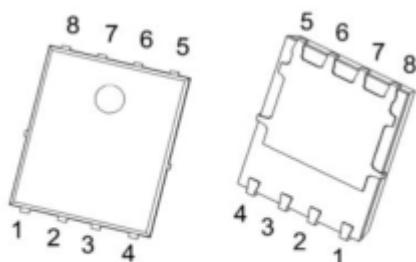
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- AEC-Q101 qualified
- 100% Single Pulse avalanche energy Test

Applications

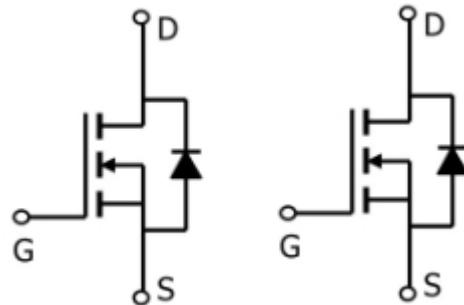
- Power switching application
- Isolated DC/DC Converters in Telecom and Industrial

Package

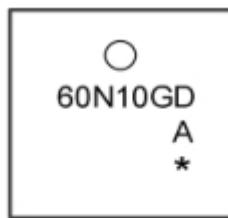


PDFN5X6-8L

Circuit diagram



Marking



60N10GD =Device Code
A =Automotive
***** =Month Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

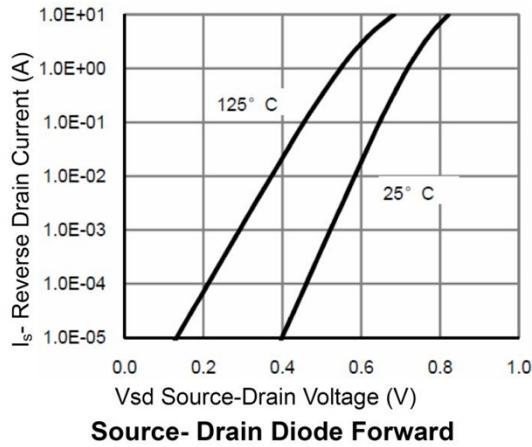
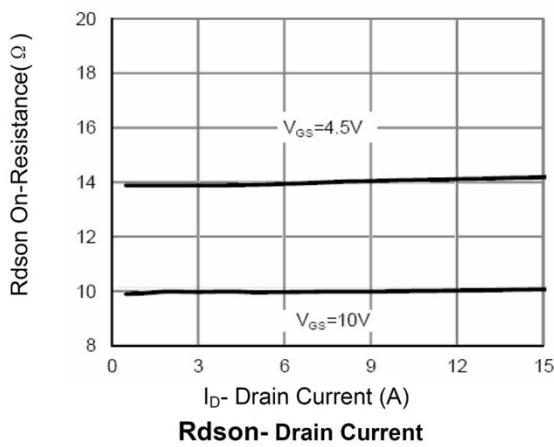
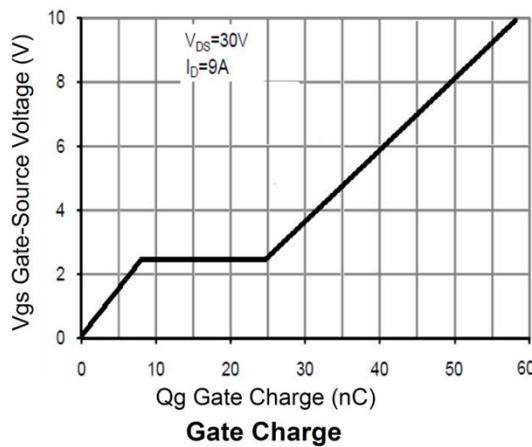
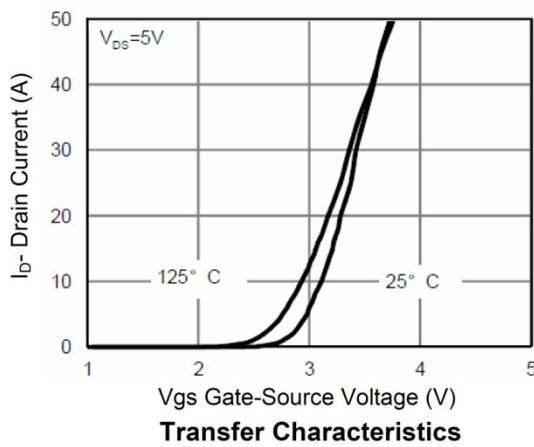
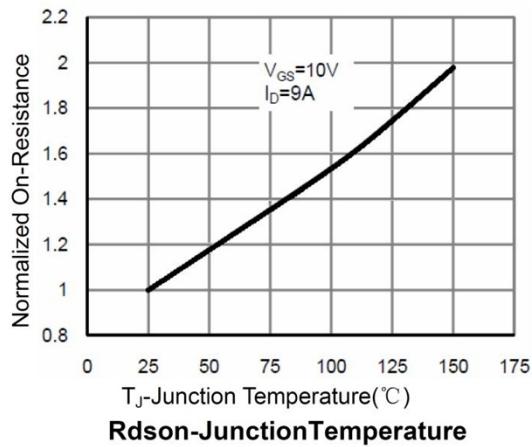
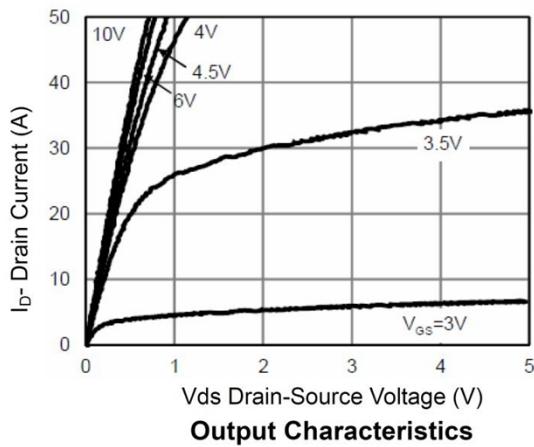
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current($T_c=25^\circ\text{C}$)	I_D	45	A
Continuous Drain Current($T_c=100^\circ\text{C}$)	I_D	34	A
Pulse Drain Current Tested	I_{DM}	180	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	60	W
Thermal Resistance-Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Maximum Junction Temperature	T_J	-55 to 175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to 175	$^\circ\text{C}$

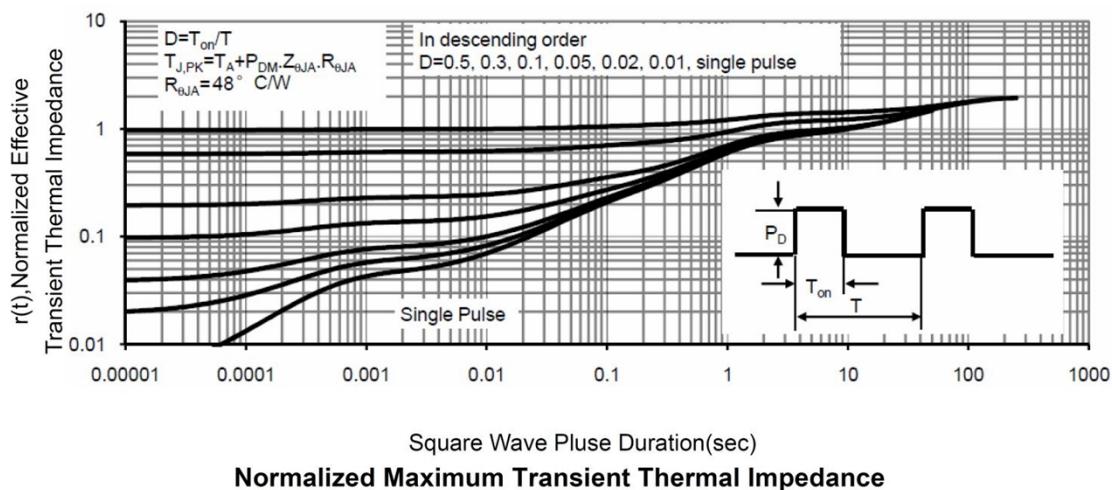
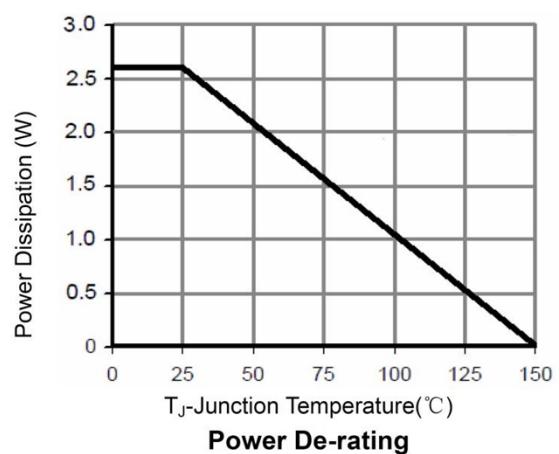
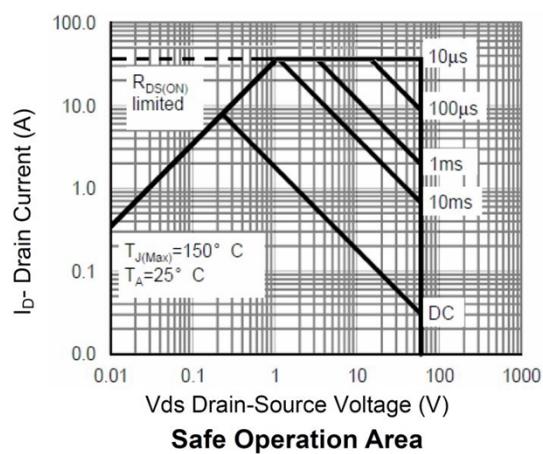
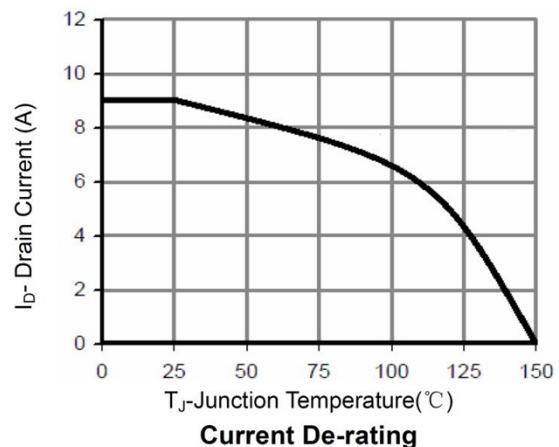
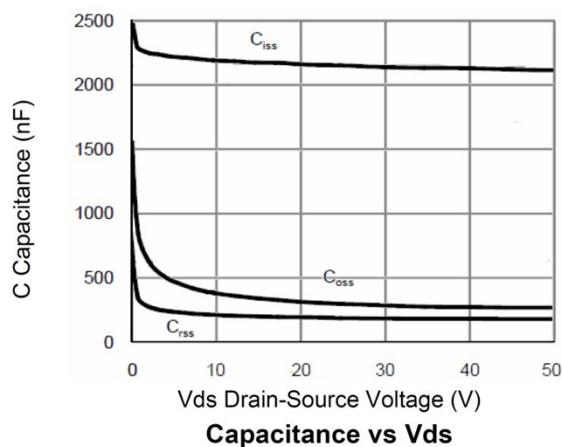
Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

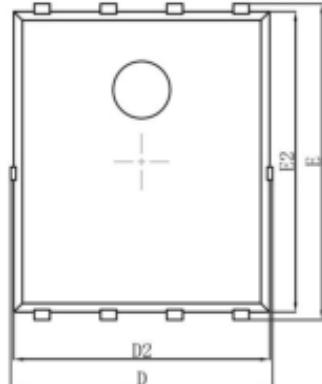
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = 9\text{A}$		10	15	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 9\text{A}$		14	18	
Dynamic and Switching Characteristics						
Input capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$		426		pF
Output capacitance	C_{oss}			103		
Reverse transfer capacitance	C_{rss}			8		
Turn-On Delay Time	$T_{d(\text{on})}$	$V_{DD}=30\text{V}, I_D = 10\text{A}, V_{GS}=10\text{V}, R_G = 1.6\Omega$		8		nS
Rise Time	T_r			5		
Turn-Off Delay Time	$T_{d(\text{off})}$			24		
Fall Time	t_f			3.5		
Total gate charge	Q_g	$V_{DS}=30\text{V}, V_{GS}=10\text{V}, I_D = 10\text{A}$		35		pF
Gate-source charge	Q_{gs}			6.4		
Gate-drain charge	Q_{gd}			3.5		
Drain-Source Body Diode Characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_S=1\text{A}$			1.2	V

Typical Characteristics

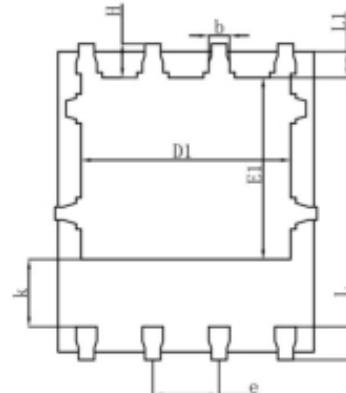




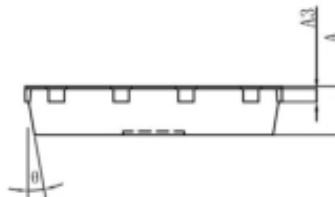
PDFN5X6-8L Package Information



Top View
[頂視圖]



Bottom View
[背視圖]



Side View
[側視圖]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°		12°	